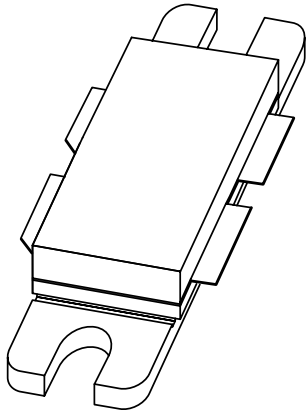


DATA SHEET



BLF861A UHF power LDMOS transistor

Preliminary specification

2000 Aug 04

UHF power LDMOS transistor

BLF861A

FEATURES

- High power gain
- Easy power control
- Excellent ruggedness
- Designed to withstand abrupt load mismatch errors
- Source on underside eliminates DC isolators; reducing common mode inductance
- Designed for broadband operation (UHF band)
- Internal input and output matching for high gain and optimum broadband operation.

APPLICATIONS

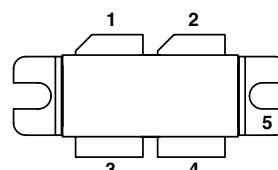
- Communication transmitter applications in the UHF frequency range.

DESCRIPTION

Silicon N-channel enhancement mode lateral D-MOS push-pull transistor in a SOT540A package with ceramic cap. The common source is connected to the mounting flange.

PINNING - SOT540A

PIN	DESCRIPTION
1	drain 1
2	drain 2
3	gate 1
4	gate 2
5	source connected to flange



Top view

MBK777

Fig.1 Simplified outline.

QUICK REFERENCE DATA

RF performance at $T_h = 25^\circ\text{C}$ in a common source 860 MHz test circuit.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η_D (%)	ΔG_p (dB)
CW, class-AB	860	32	150	>13.5 typ. 14.5	>50	≤1
PAL BG (TV); class-AB	860 (ch 69)	32	>150 typ. 170 (peak sync)	>14	>40	note 1

Note

1. Sync compression: input sync ≥ 33%; output sync 27%.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DS}	drain-source voltage		–	65	V
V _{GS}	gate-source voltage		–	±15	V
I _D	drain current (DC)		–	18	A
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C	–	318	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	200	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_{mb} = 25\ ^\circ\text{C}$; $P_{tot} = 318\ \text{W}$	0.55	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink		0.2	K/W

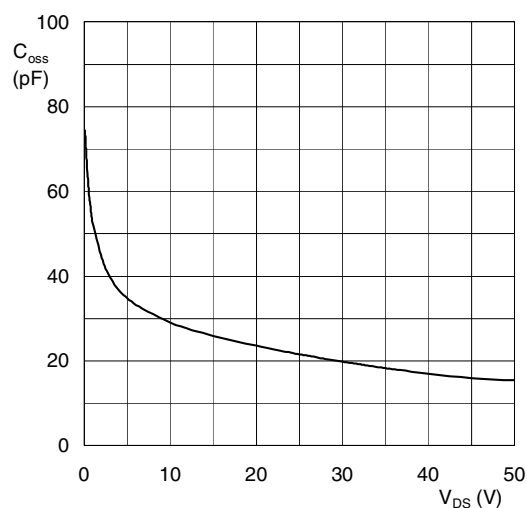
CHARACTERISTICS

$T_j = 25\ ^\circ\text{C}$; per section; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0$; $I_D = 1.5\ \text{mA}$	65	–	–	V
V_{GSth}	gate-source threshold voltage	$V_{DS} = 10\ \text{V}$; $I_D = 150\ \text{mA}$	4	–	5.5	V
I_{DSS}	drain-source leakage current	$V_{GS} = 0$; $V_{DS} = 32\ \text{V}$	–	–	2.2	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GSth} + 9\ \text{V}$; $V_{DS} = 10\ \text{V}$	18	–	–	A
I_{GSS}	gate leakage current	$V_{GS} = \pm 15\ \text{V}$; $V_{DS} = 0$	–	–	25	nA
g_{fs}	forward transconductance	$V_{DS} = 10\ \text{V}$; $I_D = 4\ \text{A}$	–	4	–	S
R_{DSon}	drain-source on-state resistance	$V_{GS} = V_{GSth} + 9\ \text{V}$; $I_D = 4\ \text{A}$	–	160	–	m Ω
C_{iss}	input capacitance	$V_{GS} = 0$; $V_{DS} = 32\ \text{V}$; $f = 1\ \text{MHz}$ ⁽¹⁾	–	82	–	pF
C_{oss}	output capacitance	$V_{GS} = 0$; $V_{DS} = 32\ \text{V}$; $f = 1\ \text{MHz}$ ⁽¹⁾	–	40	–	pF
C_{rss}	feedback capacitance	$V_{GS} = 0$; $V_{DS} = 32\ \text{V}$; $f = 1\ \text{MHz}$ ⁽¹⁾	–	6	–	pF

Note

1. Capacitance values without internal matching.



$V_{GS} = 0$; $f = 1\ \text{MHz}$; $T_j = 25\ ^\circ\text{C}$.

Fig.2 Output capacitance as a function of drain-source voltage; typical values per section.

UHF power LDMOS transistor

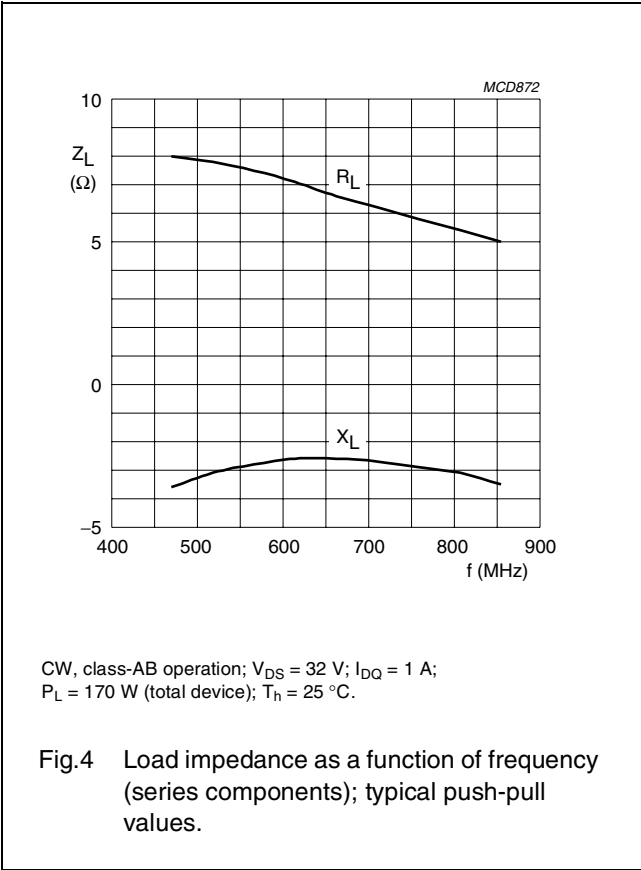
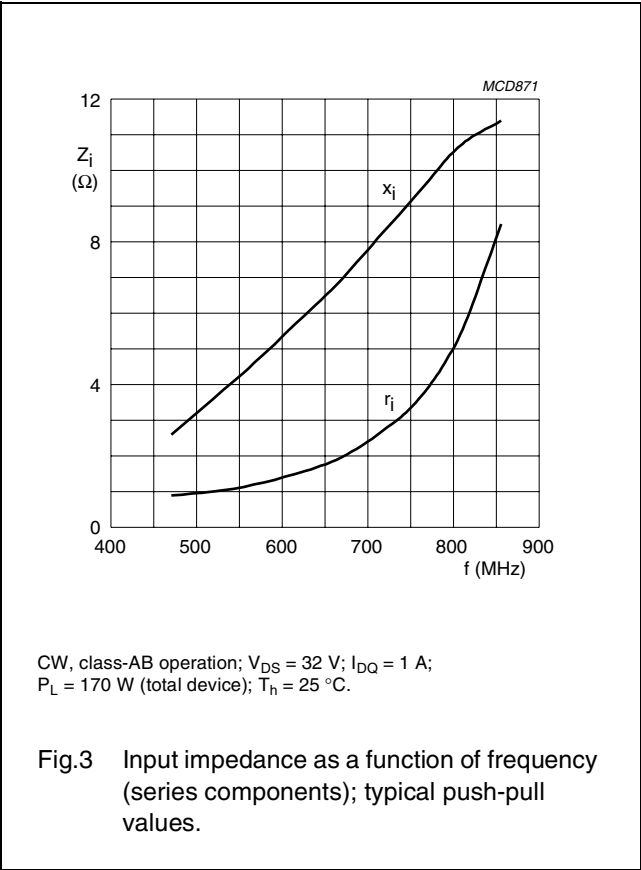
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APPLICATION INFORMATION
RF performance in a common source 860 MHz test circuit. $T_h = 25\text{ }^{\circ}\text{C}$; $R_{th\text{ mb-h}} = 0.15\text{ K/W}$; unless otherwise specified.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	I _{DQ} (A)	P _L (W)	G _p (dB)	η _D (%)	d _{Im} (dBc)	ΔG _p (dB)
CW; class-AB	860	32	1	150	>13.5 typ. 14.5	>50	–	≤1
2-tone; class-AB	f ₁ = 860 f ₁ = 860.1	32	1	150 (PEP)	>14	>40	≤–25	–
PAL BG (TV); class-AB	860 (ch 69)	32	1	> 150 typ. 170 (peak sync)	>14	>40	–	note 1

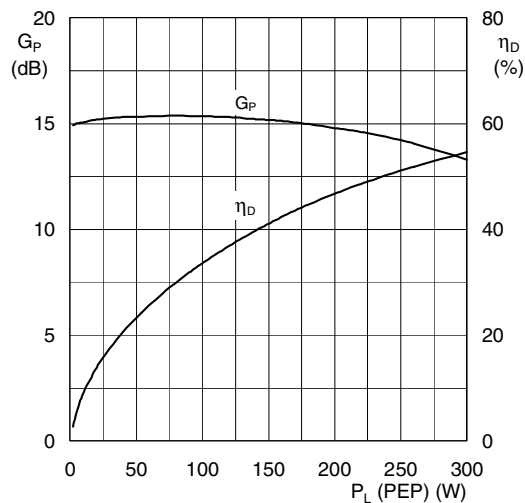
Note
1. Sync compression: input sync ≥ 33%; output sync 27% measured in 860 MHz test circuit.

Ruggedness in class-AB operation
The BLF861A is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; f = 860 MHz at rated load power.
The BLF861A is an improved version of the BLF861 on ruggedness and is capable to withstand abrupt source or load mismatch errors under the nominal power condition.



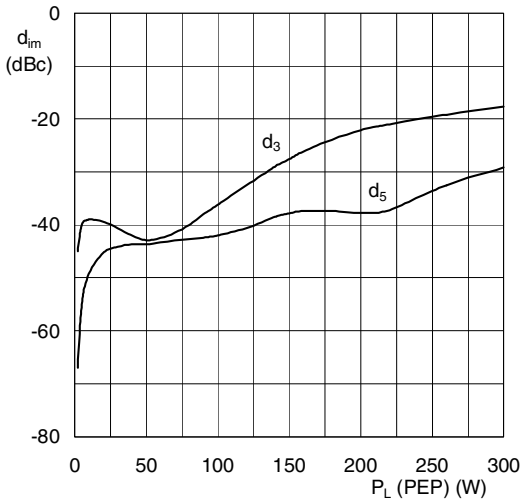
UHF power LDMOS transistor

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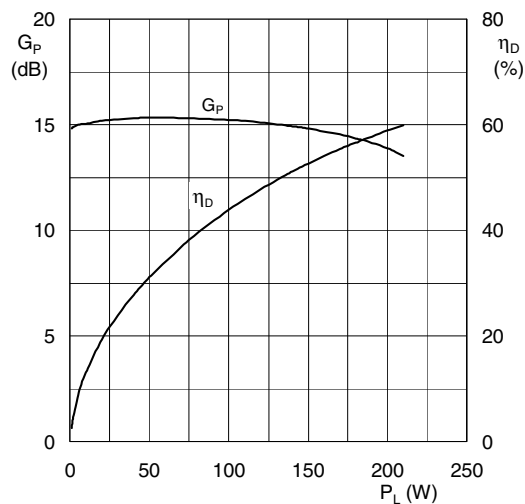
$T_h = 25\text{ }^{\circ}\text{C}$; $V_{DS} = 32\text{ V}$; $I_{DQ} = 1\text{ A}$.
2-tone: $f_1 = 860\text{ MHz}$ (−6 dB); $f_2 = 860.1\text{ MHz}$ (−6 dB)
measured in 860 MHz test circuit.

Fig.5 Power gain and drain efficiency as functions of peak envelope load power; typical values.



$T_h = 25\text{ }^{\circ}\text{C}$; $V_{DS} = 32\text{ V}$; $I_{DQ} = 1\text{ A}$.
2-tone: $f_1 = 860\text{ MHz}$ (−6 dB); $f_2 = 860.1\text{ MHz}$ (−6 dB)
measured in 860 MHz test circuit.

Fig.6 Intermodulation distortion as a function of peak envelope output power; typical values.



$T_h = 25\text{ }^{\circ}\text{C}$; $V_{DS} = 32\text{ V}$; $I_{DQ} = 1\text{ A}$; CW, class-AB; $f = 860\text{ MHz}$;
measured in 860 MHz test circuit.

Fig.7 Power gain and drain efficiency as functions of load power; typical values.

UHF power LDMOS transistor

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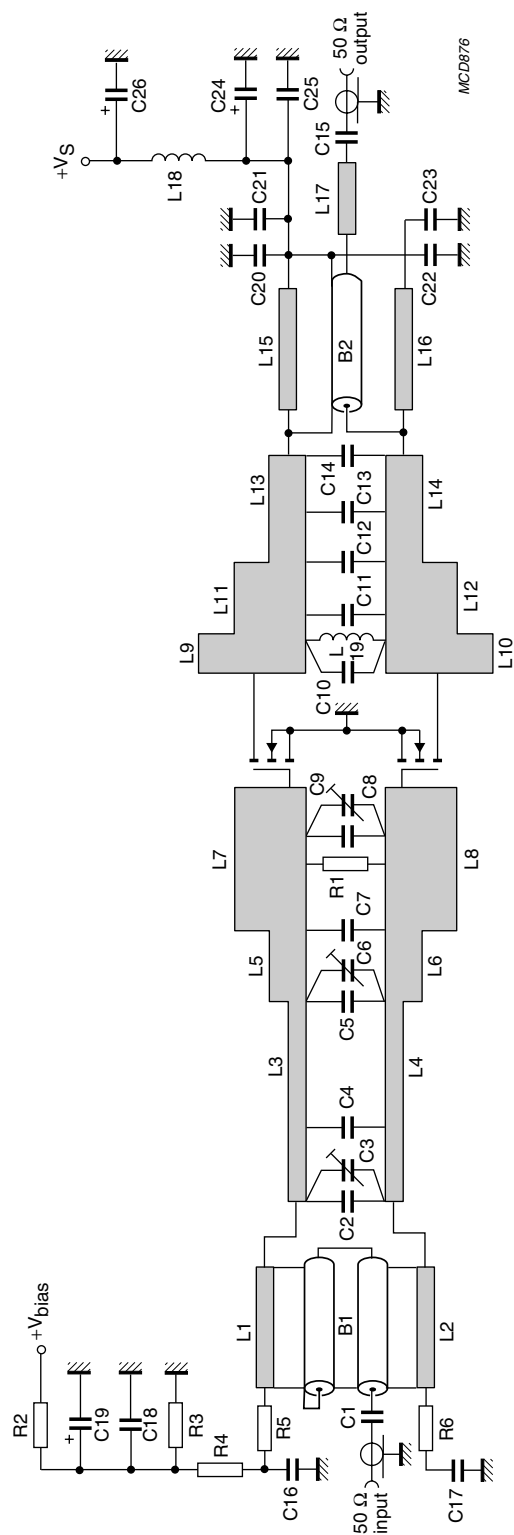


Fig.8 Class-AB common source broadband test circuit.

UHF power LDMOS transistor

BLF861A

List of components class-AB broadband test circuit (see Figs 8 and 9)

COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
C1	multilayer ceramic chip capacitor; note 1	20 pF		
C2	multilayer ceramic chip capacitor; note 1	4.3 pF		
C3, C6, C9	tekelec trimmer	0.6 to 4.5 pF		
C4	multilayer ceramic chip capacitor; note 1	9.1 pF		
C5	multilayer ceramic chip capacitor; note 1	10 pF		
C7	multilayer ceramic chip capacitor; note 1	5.1 pF		
C8	multilayer ceramic chip capacitor; note 1	13 pF		
C10, C11	multilayer ceramic chip capacitor; note 2	8.2 pF		
C12, C13	multilayer ceramic chip capacitor; note 2	6.8 pF		
C14	multilayer ceramic chip capacitor; note 3	1 pF		
C15	multilayer ceramic chip capacitor; note 3	20 pF		
C16, C17	multilayer ceramic chip capacitor	1 nF		
C18	multilayer ceramic chip capacitor	100 nF		
C19, C26	multilayer ceramic chip capacitor	100 μ F		
C20, C21, C22, C23	multilayer ceramic chip capacitor; note 2	100 pF		
C24	electrolytic capacitor	1 000 μ F		
C25	multilayer ceramic chip capacitor	1 μ F		2222 595 16754
L1, L2	stripline; note 4		30.6 $\times$ 2.4 mm	
L3, L4	stripline; note 4		28 $\times$ 2.4 mm	
L5, L6	stripline; note 4		10 $\times$ 5 mm	
L7, L8	stripline; note 4		20 $\times$ 10 mm	
L9, L10	stripline; note 4		5.5 $\times$ 15 mm	
L11, L12	stripline; note 4		10 $\times$ 10 mm	
L13, L14	stripline; note 4		15 $\times$ 5 mm	
L15, L16	stripline; note 4		48.5 $\times$ 2.4 mm	
L17	stripline; note 4		10 $\times$ 2.4 mm	
L18	ferrite			
L19	wire inductor (hairpin)		length = 17 mm	
B1	semi rigid coax balun UT70-25	$Z = 25 \Omega \pm 1.5 \Omega$	70 mm	
B2	semi rigid coax balun UT70-25	$Z = 25 \Omega \pm 1.5 \Omega$	48.5 mm	

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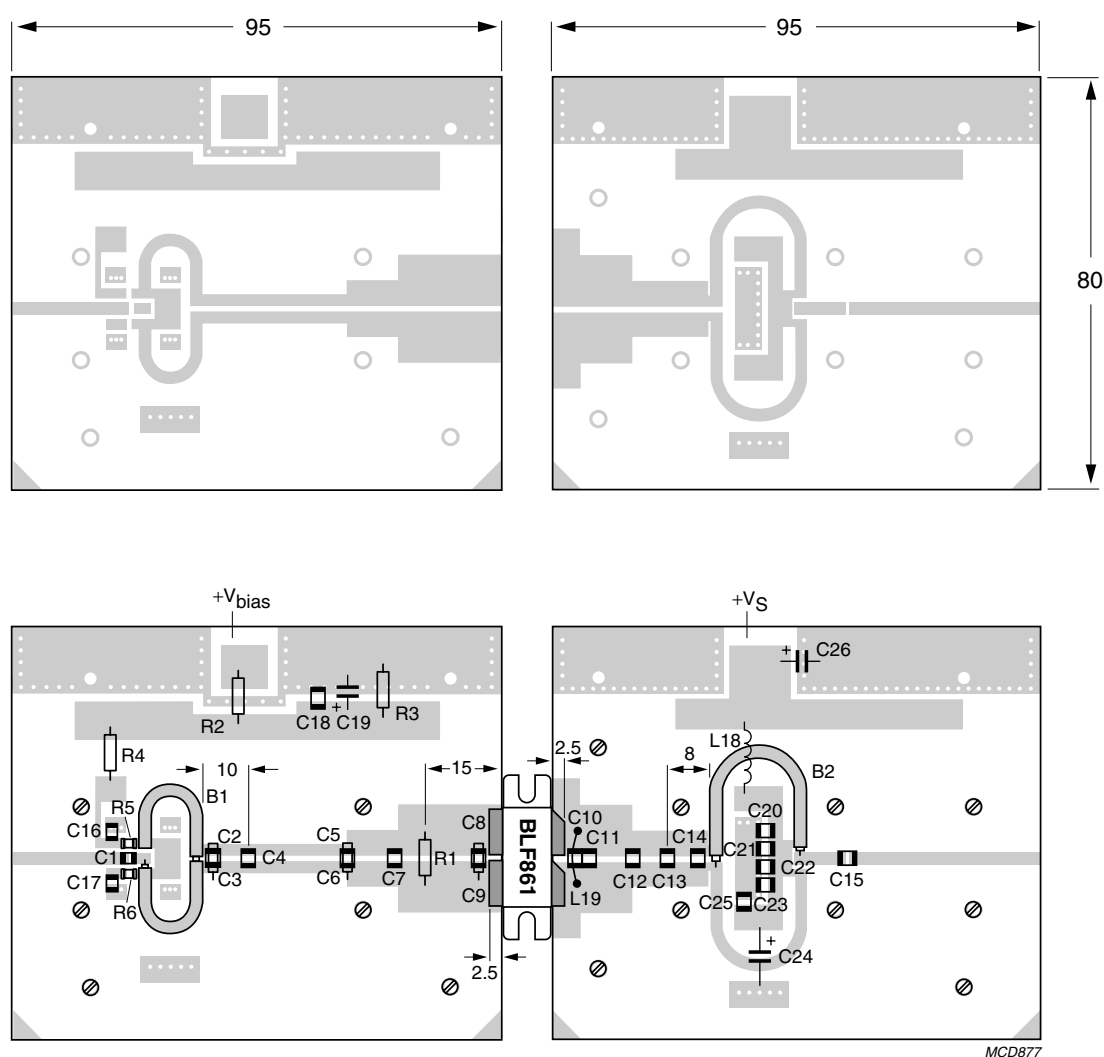
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
R1	resistor	33 Ω		
R2	resistor	1 k Ω		
R3	resistor	100 k Ω		
R4	resistor	100 Ω		
R5, R6	SMD resistor	3.9 Ω		

Notes

1. American Technical Ceramics type 100A or capacitor of same quality.
2. American Technical Ceramics type 180R or capacitor of same quality.
3. American Technical ceramics type 100B or capacitor of same quality.
4. The striplines are on a double copper-clad printed-circuit board: Rogers 5880 ($\epsilon_r = 2.2$); thickness 0.79 mm.

UHF power LDMOS transistor

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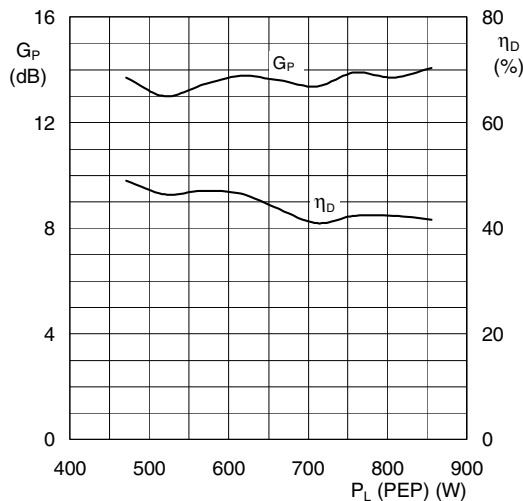
Dimensions in mm.

The components are situated on one side of the Rogers 5880 printed-circuit board, the other side is unetched and serves as a ground plane. Earth connections from the component side to the ground plane are made by through metallization.

Fig.9 Printed-circuit board and component layout for class-AB broadband test circuit.

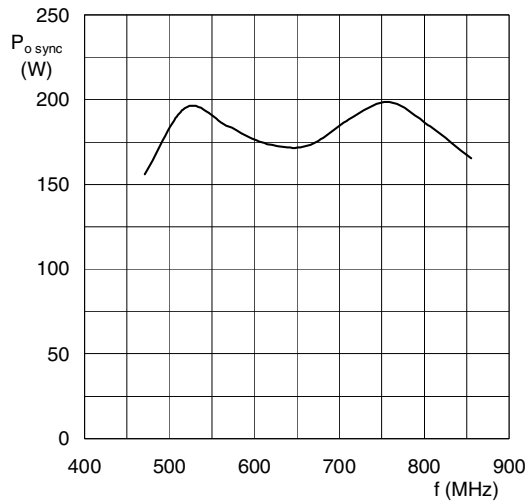
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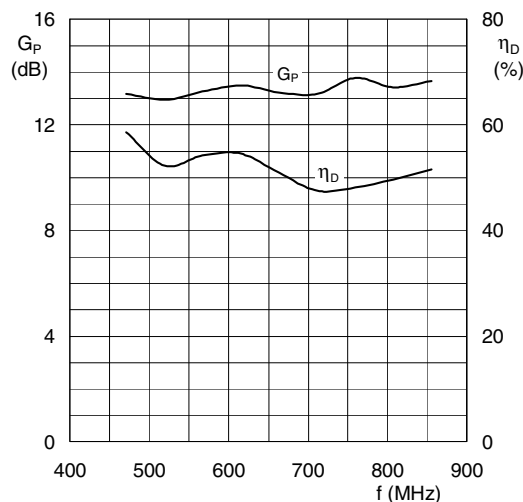
$T_h = 25\text{ }^{\circ}\text{C}$; $V_{CE} = 32\text{ V}$; $I_{DQ} = 1\text{ A}$; PAL BG signal (TV);
sync compression: input 33%, output 27%;
measured in broadband test circuit.

Fig.10 Power gain and drain efficiency as functions of frequency; typical values.



$T_h = 25\text{ }^{\circ}\text{C}$; $V_{CE} = 32\text{ V}$; $I_{DQ} = 1\text{ A}$; PAL BG signal (TV);
sync compression: input 33%, output 27%;
measured in broadband test circuit.

Fig.11 Peak envelope sync power as a function of frequency; typical values.



$T_h = 25\text{ }^{\circ}\text{C}$; $V_{DS} = 32\text{ V}$; $I_{DQ} = 1\text{ A}$; CW, class-AB operation;
 $P_L = 150\text{ W}$; measured in broadband test circuit.

Fig.12 Power gain and drain efficiency as functions of frequency; typical values.

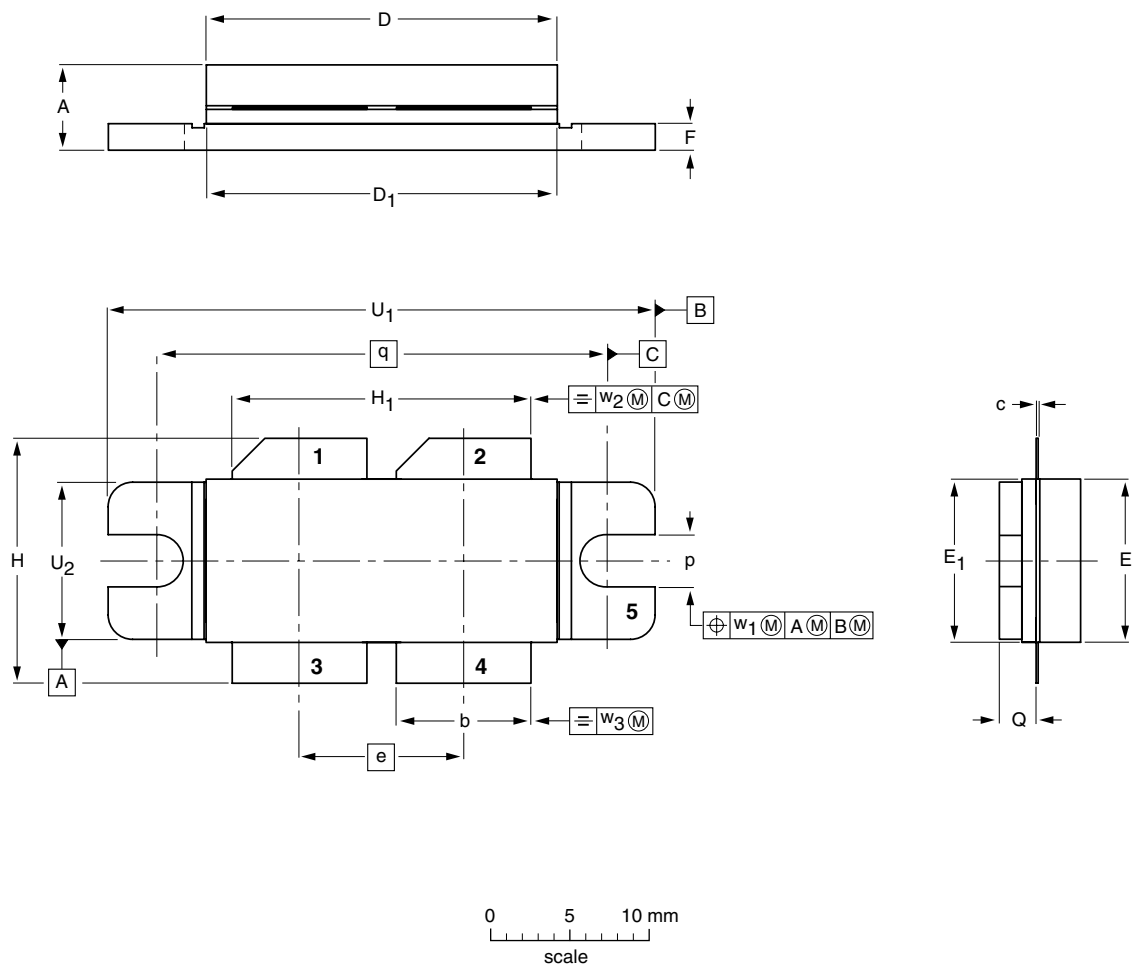
UHF power LDMOS transistor

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PACKAGE OUTLINE

Flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads

SOT540A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	e	E	E ₁	F	H	H ₁	p	Q	q	U ₁	U ₂	w ₁	w ₂	w ₃
mm	5.77 5.00	8.51 8.26	0.15 0.10	22.05 21.64	22.05 21.64	10.21	10.26 10.06	10.31 10.01	1.78 1.52	15.75 14.73	18.72 18.47	3.38 3.12	2.72 2.46	27.94	34.16 33.91	9.91 9.65	0.25	0.51	0.25
inches	0.227 0.197	0.335 0.325	0.006 0.004	0.868 0.852	0.868 0.852	0.402	0.404 0.396	0.406 0.394	0.070 0.060	0.620 0.580	0.737 0.727	0.133 0.123	0.107 0.097	1.100	1.345 1.335	0.390 0.380	0.010	0.020	0.010

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT540A						99-08-27 99-12-28

UHF power LDMOS transistor

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

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DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device.

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